

TOSHIBA Bi-CMOS INTEGRATED CIRCUIT SILICON MONOLITHIC

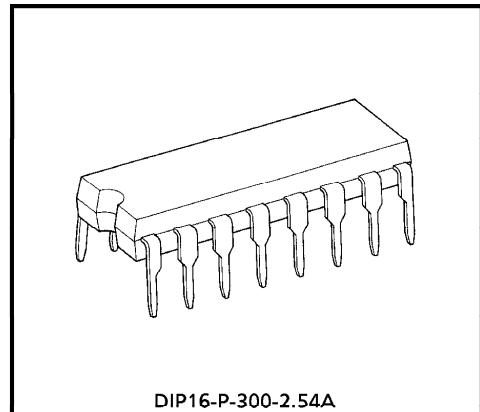
**T B 6 5 0 1 P****Bridge Driver with Rotation Detector**

The TB6501P is Bridge Driver.

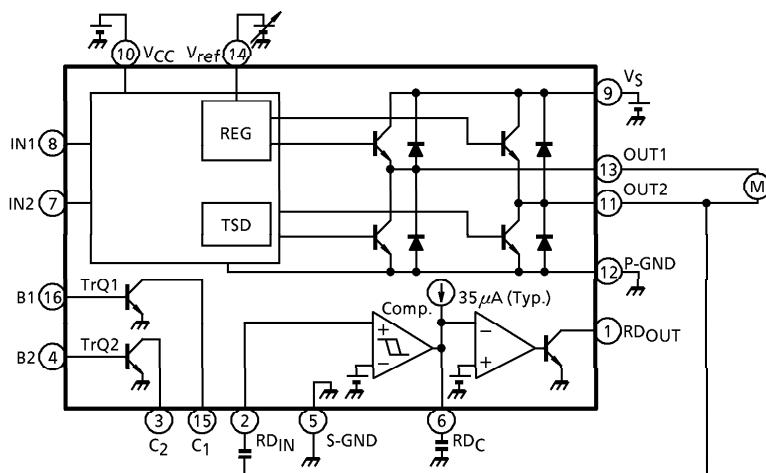
Forward Rotation, Reverse Rotation, Stop and Breaking Operations are available.

**FEATURES**

- TB6501P has RD (Rotation Detector).
- Output current up to 0.4A (AVE.) to 1.0A (PEAK).
- Wide Range of Operating Supply Voltage  
 $V_{CC}(\text{opr.}) = 4.5\sim 20V$   
 $V_S(\text{opr.}) = 0\sim 20V$   
 $V_{ref}(\text{opr.}) = 0\sim 20V \ (V_{ref} \leq V_S)$
- Thermal shutdown, Over current protector, and Standby circuit built in.



Weight : 1.11g (Typ.)

**BLOCK DIAGRAM**

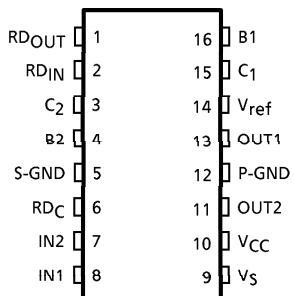
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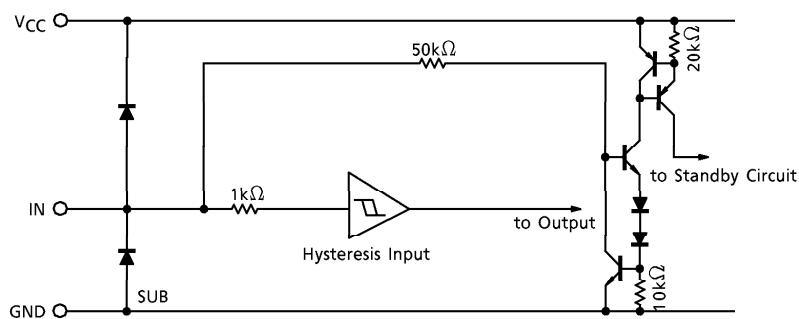
## PIN FUNCTION

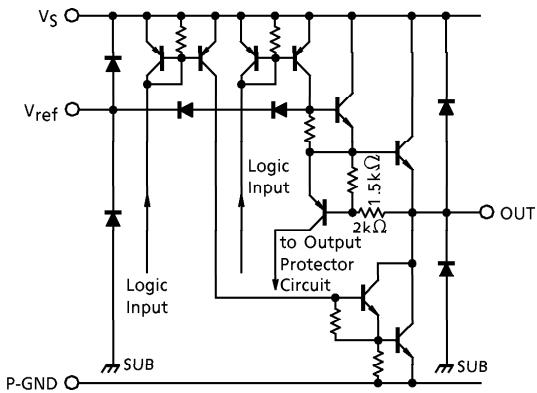
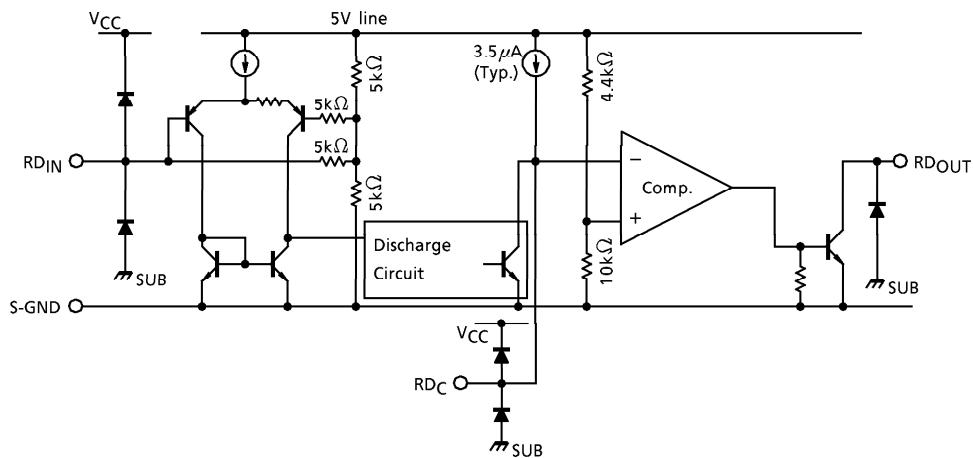
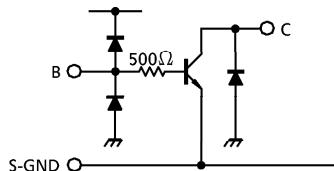
PIN No.	SYMBOL	FUNCTIONAL DESCRIPTION
1	RDOUT	Rotation detector output terminal
2	RDIN	Rotation detector input terminal
3	C <sub>2</sub>	NPN transistor collector terminal
4	B2	NPN transistor base terminal
5	S-GND	Signal GND terminal
6	RD <sub>C</sub>	Rotation detector capacitor connection terminal
7	IN2	Input 2 terminal
8	IN1	Input 1 terminal
9	V <sub>S</sub>	Power voltage supply terminal for motor driver
10	V <sub>CC</sub>	Power voltage supply terminal for logic
11	OUT2	Output 2 terminal
12	P-GND	Power GND terminal
13	OUT1	Output 1 terminal
14	V <sub>ref</sub>	Power voltage supply terminal for controller
15	C <sub>1</sub>	NPN transistor collector terminal
16	B1	NPN transistor base terminal

## PIN CONNECTION



## **INPUT CIRCUIT**



**OUTPUT CIRCUIT****ROTATION DETECTOR CIRCUIT****TrQ1, TrQ2 CIRCUIT**

**FUNCTION**

INPUT		OUTPUT		MODE
IN1	IN2	OUT1	OUT2	MOTOR
0	0	$\infty$	$\infty$	STOP
1	0	H	L	CW / CCW
0	1	L	H	CCW / CW
1	1	L	L	BRAKE

$\infty$  : High Impedance

(Note) Inputs are all high active type.

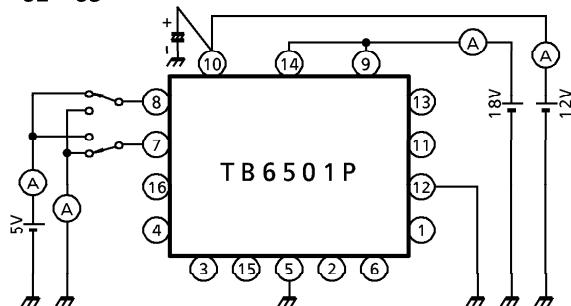
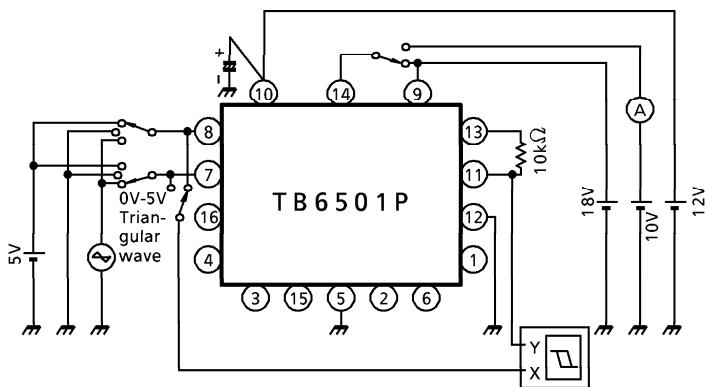
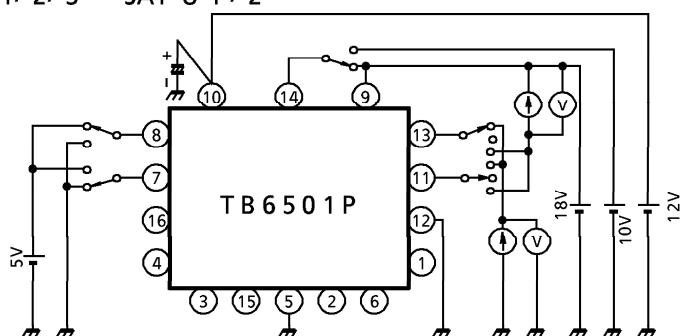
**MAXIMUM RATINGS (Ta = 25°C)**

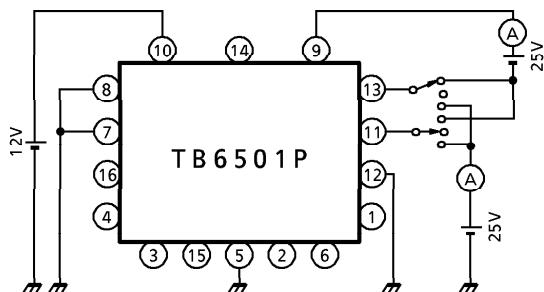
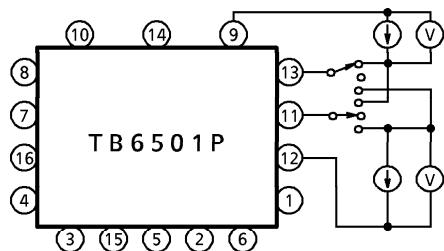
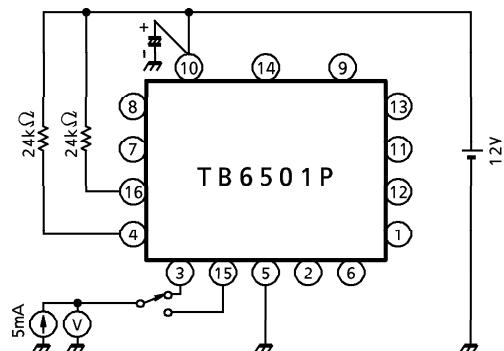
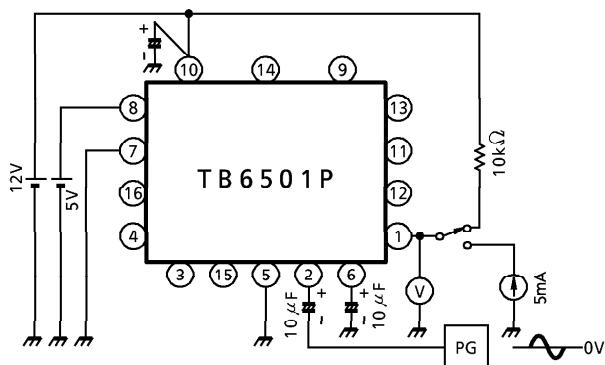
CHARACTERISTIC		SYMBOL	RATING	UNIT
Supply Voltage		V <sub>CC</sub>	25	V
Motor Drive Voltage		V <sub>S</sub>	25	V
Reference Voltage		V <sub>ref</sub>	25	V
Output Current	PEAK	I <sub>O</sub> (PEAK)	(Note) 1.0	A
	AVE.	I <sub>O</sub> (AVE.)	0.4	
	RD	I <sub>RD</sub> (PEAK)	(Note) 20	mA
	TR	I <sub>TR</sub> (PEAK)	(Note) 50	
Power Dissipation		P <sub>D</sub>	1.2	W
Operating Temperature		T <sub>opr</sub>	-30~75	°C
Storage Temperature		T <sub>stg</sub>	-55~150	°C

(Note) t = 0.1s

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ ,  $V_{CC} = 12\text{V}$ ,  $V_S = 18\text{V}$ )

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Current	$I_{CC1}$	—		Output open CW / CCW mode	—	8.2	12	mA
	$I_{CC2}$	—		Output open STOP mode	—	400	750	$\mu\text{A}$
	$I_{CC3}$	—		Output open BREAK mode	—	8.2	12	mA
	$I_S1$	—	$V_{ref} = V_S$	Output open CW / CCW mode	—	5.2	11	mA
	$I_S2$	—	$V_{ref} = V_S$	Output open STOP mode	—	0	50	$\mu\text{A}$
	$I_S3$	—	$V_{ref} = V_S$	Output open BREAK mode	—	6.8	13	mA
Input Operating Voltage	1 (High)	$V_{IN1}$	—	$T_j = 25^\circ\text{C}$	3.5	—	5.5	V
	2 (Low)	$V_{IN2}$	—	$T_j = 25^\circ\text{C}$	GND	—	0.8	
Input Current		$I_{IN}$	—	シンク $V_{IN} = 5\text{V}$	—	37	80	$\mu\text{A}$
Input Hysteresis Voltage		$\Delta V_T$	—	—	—	0.55	—	V
Saturation Voltage	$V_{SAT U-1}$	—	$V_{ref} = V_S$ $I_O = 0.2\text{A}$	Output $V_S$ CW / CCW mode	—	1.6	—	V
	$V_{SAT L-1}$	—	$V_{ref} = V_S$ $I_O = 0.2\text{A}$	Output GND CW / CCW mode	—	0.8	—	V
	$V_{SAT U-2}$	—	$V_{ref} = V_S$ $I_O = 0.4\text{A}$	Output $V_S$ CW / CCW mode	—	1.75	2.3	V
	$V_{SAT L-2}$	—	$V_{ref} = V_S$ $I_O = 0.4\text{A}$	Output GND CW / CCW mode	—	0.9	1.3	V
	$V_{SAT U-3}$	—	$V_{ref} = V_S$ $I_O = 1.0\text{A}$	Output $V_S$ CW / CCW mode	—	2.25	2.6	V
	$V_{SAT L-3}$	—	$V_{ref} = V_S$ $I_O = 1.0\text{A}$	Output GND CW / CCW mode	—	1.2	1.6	V
Output Voltage	$V_{SAT U-1'}$	—	$V_{ref} = 10\text{V}$ $I_O = 0.2\text{A}$	Output GND CW / CCW mode	9.3	10	10.7	V
	$V_{SAT U-2'}$	—	$V_{ref} = 10\text{V}$ $I_O = 0.4\text{A}$	Output GND CW / CCW mode	9.3	10	10.7	V
Leaking Current	$I_{LU}$	—	$V_L = 25\text{V}$	—	0	50	$\mu\text{A}$	
	$I_{LL}$	—	$V_L = 25\text{V}$	—	0	50		
Diode Forward Voltage	Upper	$V_F U-1$	—	$I_F = 0.4\text{A}$	—	1.5	—	V
		$V_F U-2$	—	$I_F = 1\text{A}$	—	2.5	—	
	Lower	$V_F L-1$	—	$I_F = 0.4\text{A}$	—	1.0	—	
		$V_F L-2$	—	$I_F = 1\text{A}$	—	1.3	—	
Reference Current		$I_{ref}$	—	$V_{ref} = 10\text{V}$ Source Typ.	—	1	—	mA
RD Output Saturation Voltage		$V_{SAT RD}$	—	$I_{RD} = 5\text{mA}$	—	0.18	0.35	V
TR Output Saturation Voltage		$V_{SAT TR}$	—	$I_{TR} = 10\text{mA}$	—	4	0.65	V
RDC Charge Current		$I_{RDC}$	—	—	21	35	55	$\mu\text{A}$
RD Detective Sensitivity	Detective Level	$RD(\text{ON})$	—	AC coupling sine wave input $RDC = 10\mu\text{F}$	14	—	—	mV
	Undetective Level	$RD(\text{OFF})$	—		—	—	7	
Thermal Shutdown Operating Temperature		$T_{TSD}$	—	$T_j$	160	—	—	°C

**TEST CIRCUIT 1** $I_{CC1}, I_{CC2}, I_{CC3}, I_{IN}, I_S1, I_S2, I_S3$ **TEST CIRCUIT 2** $V_{IN1}, V_{IN2}, \Delta V_T$ **TEST CIRCUIT 3** $V_{SAT\ U-1, 2, 3}, V_{SAT\ L-1, 2, 3}, V_{SAT\ U-1', 2'}$ (Note) Calibrate  $I_O$  to 0.2 / 0.4 / 1.0A by  $R_L$ .

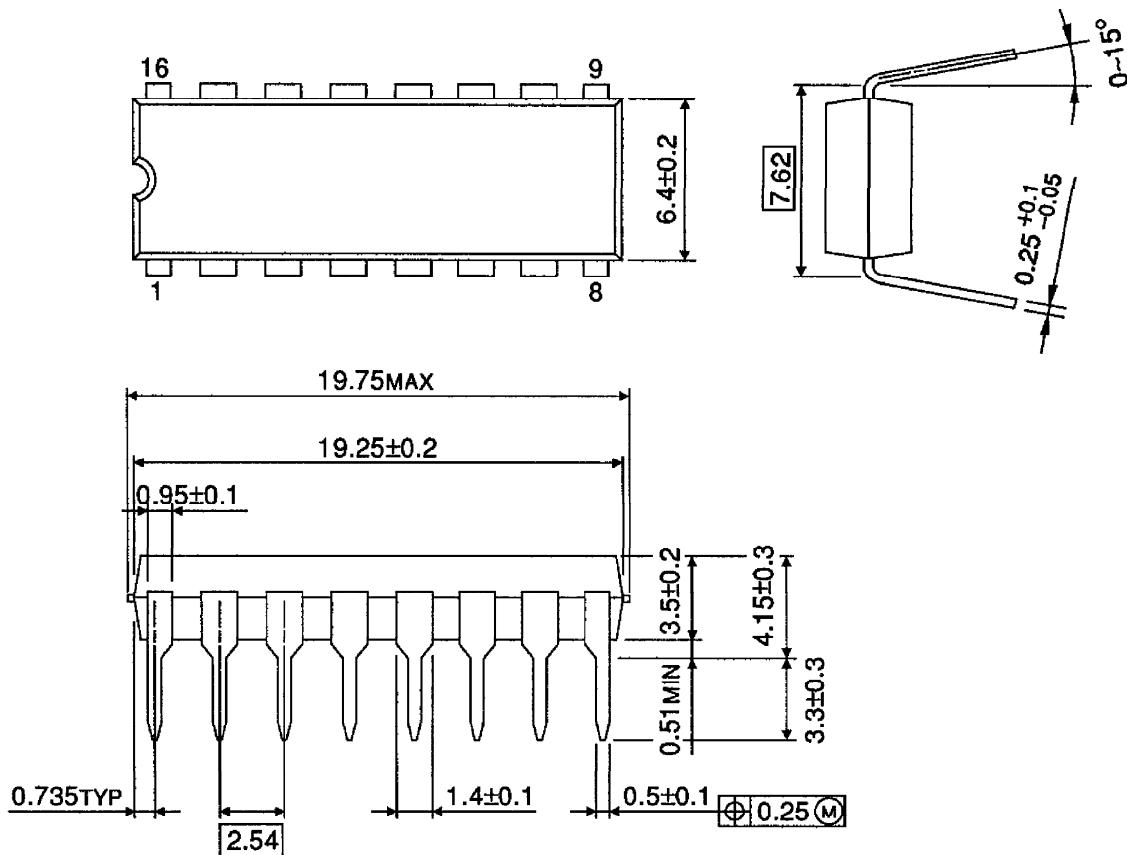
**TEST CIRCUIT 4** $I_{LU}, I_{LL}$ **TEST CIRCUIT 5** $V_F\ U-1, 2 \quad V_F\ L-1, 2$ **TEST CIRCUIT 6** $V_{SAT\ TR.}$ **TEST CIRCUIT 7** $V_{SAT\ RD} \quad RD\ Sensitivity$ 

(Note) Utmost care is necessary in the design of the output line,  $V_S$ ,  $V_{CC}$  and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

## OUTLINE DRAWING

DIP16-P-300-2.54A

Unit : mm



Weight : 1.11g (Typ.)